

Attorney Docket No. 040021-0306970
Client Reference: OPP 030892 US

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: KWAN-JU KOH

Application No.:	Confirmation No:
Filed: December 3, 2003	Group No.:
	Examiner
For: MOS TRANSISTOR AND FABRICATION METHOD THEREOF	

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

APPLICATION DATA SHEET
37 C.F.R. § 1.76

BIBLIOGRAPHIC DATA

1. Applicant information

First applicant: KWAN-JU KOH
Citizenship: KOREA
Residence: Seoul, Korea

2. Correspondence information

Correspondence for this application should be addressed as follows:

Customer No.: 00909

3. Application information

Title of Invention: MOS TRANSISTOR AND FABRICATION METHOD THEREOF

Docket number assigned to this application: 040021-0306970

Suggested Classification: Class:
Subclass:
Technology Center to which subject matter is assigned:

Total number of drawing sheets: 2

Type of application:

Utility

Application is to be published. Suggested drawing figure for publication: **2E**

Secrecy order under § 5.2:

This application does not disclose subject matter of an application which is under a secrecy order pursuant to § 5.2.

4. Representative information

The following have a power of attorney or authorization of agent in this application:

Customer No.: 00909

5. Foreign priority information

Foreign priority is claimed for this application as follows:

Country: KOREA
Application No.: 10-2002-0076823
Filing Date: December 5, 2002
Status: pending

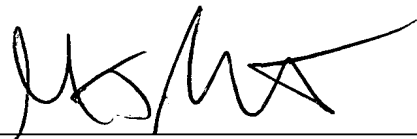
6. Assignee information

The assignee(s) of this application is/are:

Anam Semiconductor Inc.
891-10, Daechi-dong, Kangnam-ku
Seoul, 135-523
KOREA
Extent of interest of assignee in application: 100%

Date: December 3, 2003

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Signature of Practitioner
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